

### **40V N-Channel Enhancement Mode MOSFET**

Voltage 40 V Current 56 A

#### **Features**

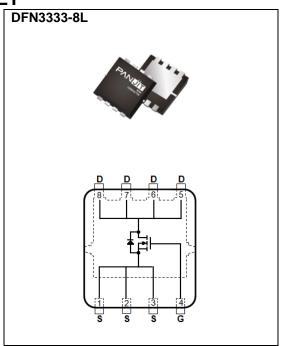
- RDS(ON), VGS@10V, ID@10A<7.4 $m\Omega$
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@7V, I<sub>D</sub>@6A<11mΩ
- Excellent FOM
- Standard Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER  |                      | SYMBOL                           | LIMIT   | UNITS |  |
|--|----------------------|----------------------------------|---------|-------|--|
| Drain-Source Voltage                               |                      | $V_{DS}$                         | 40      | V     |  |
| Gate-Source Voltage                                |                      | $V_{GS}$                         | ±20     | v     |  |
| Continuous Drain Current(Note 3)                   | T <sub>C</sub> =25°C |                                  | 56      |       |  |
|  | Tc=100°C             | l <sub>D</sub>                   | 39      | Α     |  |
| Pulsed Drain Current(Note 1)                       | T <sub>C</sub> =25°C | I <sub>DM</sub>                  | 168     |       |  |
| Power Dissipation                                  | T <sub>C</sub> =25°C | D-                               | 42      | W     |  |
|  | Tc=100°C             | Po                               | 21      |       |  |
| Continuous Drain Current(Note 4)                   | T <sub>A</sub> =25°C |                                  | 13.7    | А     |  |
|  | T <sub>A</sub> =70°C | ID                               | 11.5    |       |  |
| Power Dissipation                                  | T <sub>A</sub> =25°C | PD                               | 2.5     | W     |  |
|  | T <sub>A</sub> =70°C |                                  | 1.8     |       |  |
| Single Pulse Avalanche Current <sup>(Note 5)</sup> |                      | las                              | 6.3     | А     |  |
| Single Pulse Avalanche Energy <sup>(Note 5)</sup>  |                      | E <sub>AS</sub>                  | 18      | mJ    |  |
| Operating Junction and Storage Temperature Range   |                      | T <sub>J</sub> ,T <sub>STG</sub> | -55~175 | °C    |  |
| Thermal Resistance <sup>(Note 4)</sup>             | Junction to Case     | R <sub>θ</sub> JC                | 3.6     | °C/W  |  |
|  | Junction to Ambient  | R <sub>θJA</sub>                 | 60      |       |  |



### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER                        | SYMBOL   | TEST CONDITION                                  | MIN.                         | TYP. | MAX. | UNITS |  |
|----------------------------------|--|---|------------------------------|------|------|-------|--|
| Static                           | •  |   |                              |      |      |       |  |
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub> V <sub>GS</sub> =0V, I <sub>D</sub> =250uA |   | 40                           | -    | -    |       |  |
| Gate Threshold Voltage           | V <sub>GS(th)</sub>  | $V_{DS}=V_{GS}$ , $I_{D}=250uA$                 | 2                            | 3    | 4    | V     |  |
| Drain-Source On-State Resistance | R <sub>DS(on)</sub>  | V <sub>GS</sub> =10V, I <sub>D</sub> =10A       | -                            | 5.9  | 7.4  | 0     |  |
|                                  |  | V <sub>GS</sub> =7V, I <sub>D</sub> =6A         | 7V, I <sub>D</sub> =6A - 8.3 |      | 11   | mΩ    |  |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>   | V <sub>DS</sub> =40V, V <sub>GS</sub> =0V       | -                            | -    | 1    | uA    |  |
| Gate-Source Leakage Current      | I <sub>GSS</sub>   | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V      | -                            | -    | ±100 | nA    |  |
| Dynamic <sup>(Note 6)</sup>      | •  |   |                              |      |      |       |  |
| Total Gate Charge                | $Q_g$  | .,  | ı                            | 16   | 21   | nC    |  |
| Gate-Source Charge               | Q <sub>gs</sub>  | V <sub>DS</sub> =32V, I <sub>D</sub> =10A,      | -                            | 5.2  | -    |       |  |
| Gate-Drain Charge                | $Q_{gd}$   | V <sub>GS</sub> =10V                            | -                            | 2.5  | -    |       |  |
| Input Capacitance                | Ciss   | )/ 05)/ )/ 0)/                                  | -                            | 615  | 860  | pF    |  |
| Output Capacitance               | Coss   | V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,      | -                            | 238  | 360  |       |  |
| Reverse Transfer Capacitance     | Crss   | f=1MHz  | -                            | 14   | 25   |       |  |
| Gate resistance                  | Rg   | f=1MHz  | -                            | 1.3  | -    | Ω     |  |
| Turn-On Delay Time               | td <sub>(on)</sub>   |   | -                            | 6.4  | -    |       |  |
| Turn-On Rise Time                | tr   | V <sub>DS</sub> =32V, I <sub>D</sub> =10A,      | -                            | 5.2  | -    |       |  |
| Turn-Off Delay Time              | td <sub>(off)</sub>  | $V_{GS}=10V, R_{G}=3\Omega$ (Note 2)14          | -                            | 19   | -    | ns    |  |
| Turn-Off Fall Time               | tf   | (Note 2)14                                      | -                            | 6.6  | -    |       |  |
| Drain-Source Diode               | 1  |   |                              | •    | •    |       |  |
| Diode Forward Current            | Is   | T <sub>C</sub> =25°C                            | -                            | -    | 46   |       |  |
| Pulsed Diode Forward Current     | I <sub>SM</sub>  | (Package Limit)                                 | -                            | -    | 168  | Α     |  |
| Diode Forward Voltage            | V <sub>SD</sub>  | Is=20A, V <sub>GS</sub> =0V                     | -                            | 0.85 | 1.3  | V     |  |
| Reverse Recovery Time            | Trr  | V <sub>DD</sub> =32V,V <sub>GS</sub> =0V,       | -                            | 14   | -    | ns    |  |
| Reverse Recovery Charge          | Qrr  | I <sub>S</sub> =20A,dI <sub>S</sub> /dt=100A/us | -                            | 4    | -    | nC    |  |

#### NOTES:

- 1. Pulse width<100us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an  $R_{\theta JC}$ =3.6°C/W.
- 4. R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 5. Eas is calculated based on the condition of L=1mH, Ias=6A, V<sub>DD</sub>=30V, V<sub>GS</sub>=10V. 100% test at L=0.5mH, Ias=6.3A in production.
- 6. Guaranteed by design, not subject to production testing.



#### **TYPICAL CHARACTERISTIC CURVES**

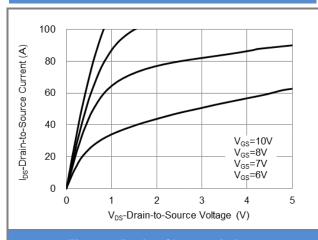
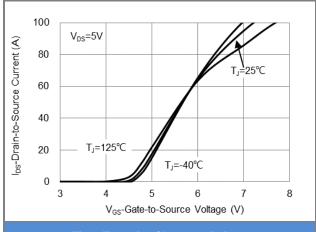


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

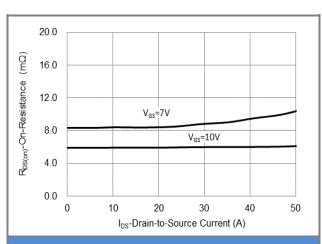


Fig.3 On-Resistance vs. Drain Current

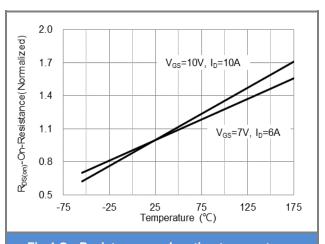
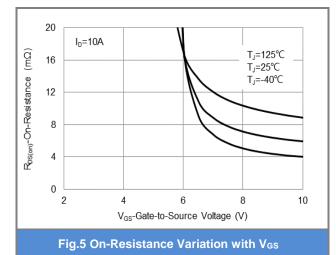


Fig.4 On-Resistance vs. Junction temperature



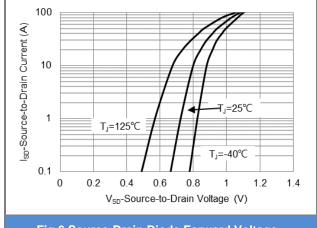


Fig.6 Source-Drain Diode Forward Voltage



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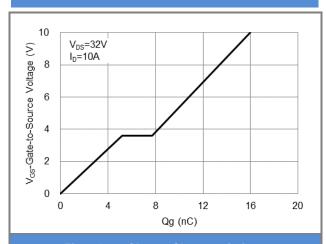


Fig.7 Gate-Charge Characteristics

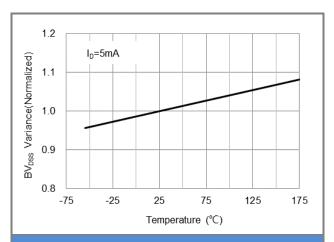


Fig.8 Breakdown Voltage Variation vs. Temperature

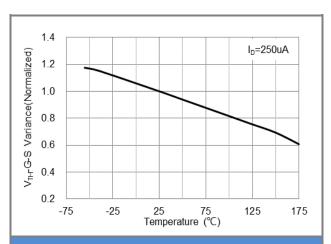


Fig.9 Threshold Voltage Variation with Temperature

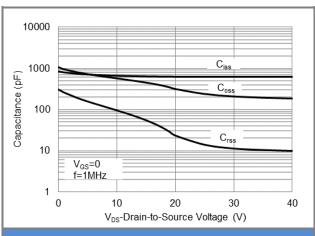
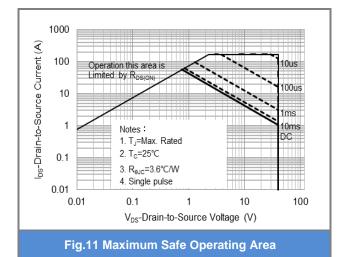


Fig.10 Capacitance vs. Drain-Source Voltage



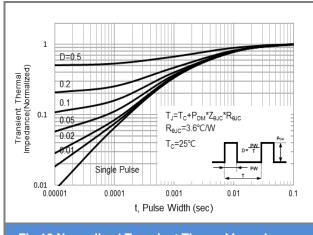


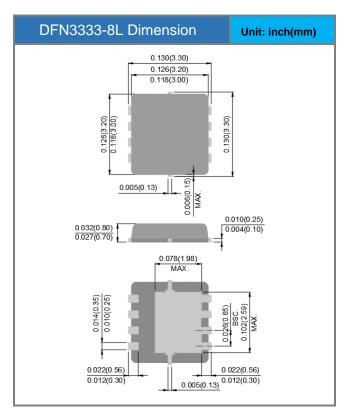
Fig.12 Normalized Transient Thermal Impedance

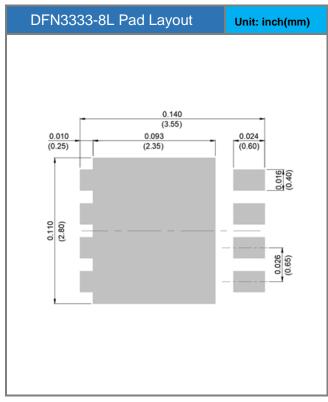


### **Product and Packing Information**

| Part No.       | Package Type | Packing Type      | Marking |  |
|----------------|--------------|-------------------|---------|--|
| PJQ4548S6VP-AU | DFN3333-8L   | 5K pcs / 13" reel | 548X    |  |

### **Packaging Information & Mounting Pad Layout**







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